

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

1N4933GPP SERIES

GLASS PASSIVATED JUNCTION
FAST RECOVERY RECTIFIER
1.0 AMP, 50 THRU 600 VOLTS

JEDEC DO-41 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 1N4933GPP Series types are 1.0 Amp Glass Passivated Junction Fast Recovery Silicon Rectifiers which are high quality, well constructed, highly reliable components designed for high speed switching applications. **THIS DEVICE IS MANUFACTURED WITH A GLASS PASSIVATED CHIP FOR OPTIMUM RELIABILITY.**
Note: Higher voltage devices are available in the CR1F-010GPP series.

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

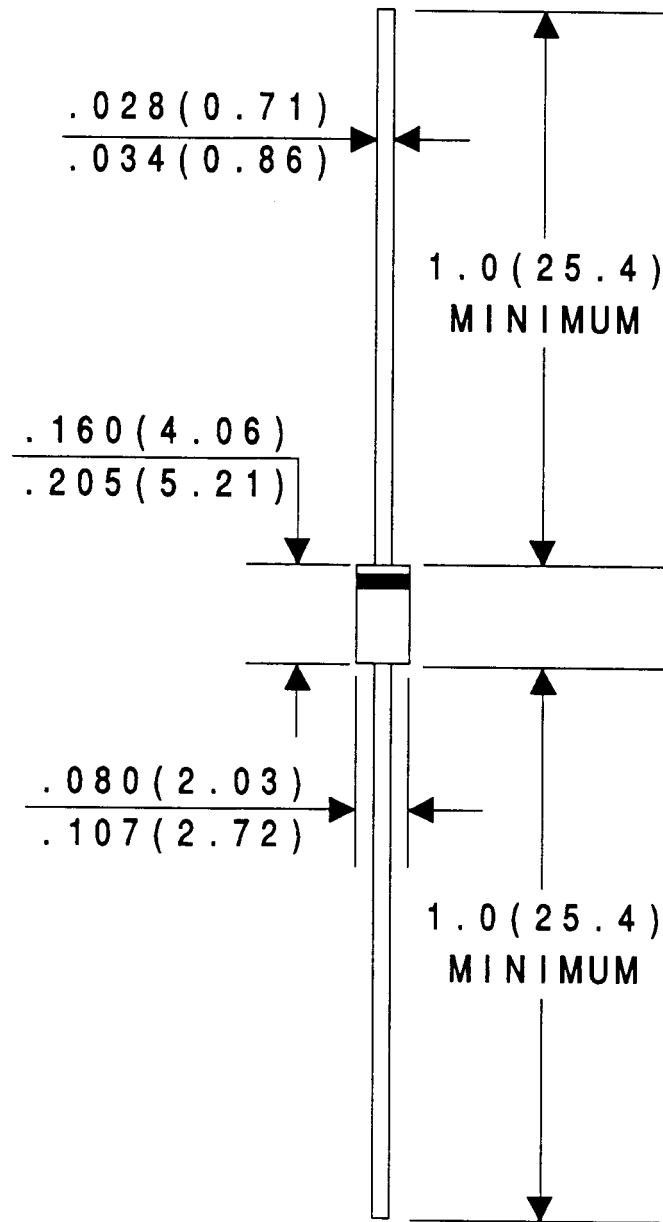
	<u>SYMBOL</u>	<u>1N4933</u> <u>GPP</u>	<u>1N4934</u> <u>GPP</u>	<u>1N4935</u> <u>GPP</u>	<u>1N4936</u> <u>GPP</u>	<u>1N4937</u> <u>GPP</u>	<u>UNITS</u>
Peak Repetitive Reverse Voltage	V_{RRM}	50	100	200	400	600	V
DC Blocking Voltage	V_R	50	100	200	400	600	V
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	V
Average Forward Current ($T_A=75^\circ\text{C}$)	I_O			1.0			A
Peak Forward Surge Current ($T_A=75^\circ\text{C}$)	I_{FSM}			30			A
Operating and Storage							
Junction Temperature	T_J, T_{stg}			-65 to +175			$^\circ\text{C}$
Thermal Resistance	θ_{JA}			50			$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>TYP</u>	<u>MAX</u>	<u>UNITS</u>
V_F	$I_F=1.0\text{A}$			1.3	V
I_R	$V_R=\text{Rated } V_{RRM}$			5.0	μA
I_R	$V_R=\text{Rated } V_{RRM}, T_A=125^\circ\text{C}$			100	μA
t_{rr}	$I_F=1.0\text{A}, V_R=30\text{V}$			200	ns
C_J	$V_R=4.0\text{V}, f=1.0\text{MHz}$		15		pF

(SEE REVERSE FOR MECHANICAL OUTLINE)

JEDEC DO-41 CASE - MECHANICAL OUTLINE



All Dimensions in Inches (mm).